

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

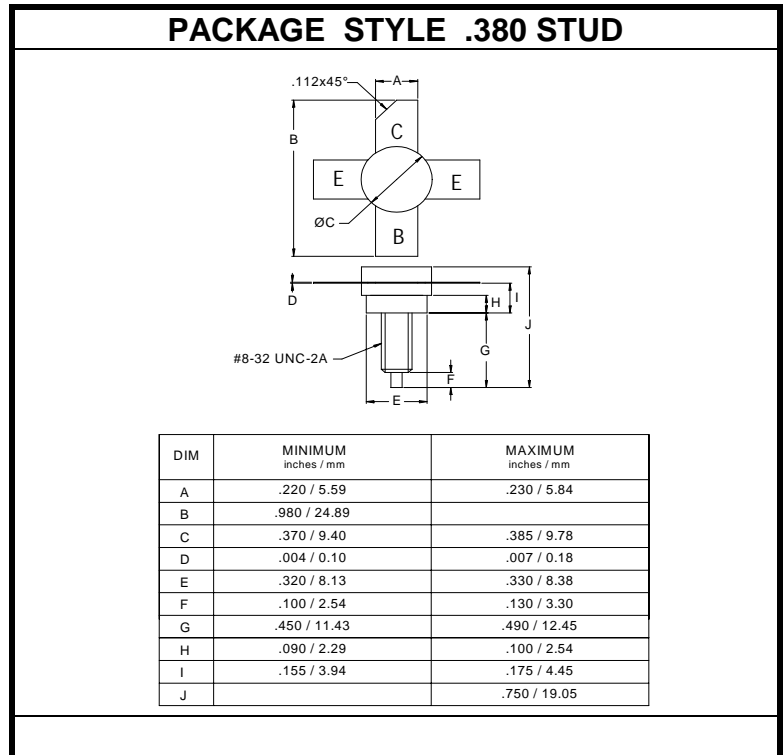
The **ASI BLX39** is Designed for broadband amplifier operations up to 175 MHz.

FEATURES:

- $P_G = 7.6$ dB min. at 40 W/175 MHz
- Emitter Resistors Ballasted
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CB}	65 V
V_{CE}	35 V
P_{DISS}	60 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.9 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CES}	$I_C = 200$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_E = 28$ V			5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz			65	pF
P_G	$V_{CE} = 28$ V $P_{IN} = 7.0$ W $f = 175$ MHz	7.6			dB
η_C		60			%

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.